

# **isc Silicon PNP Power Transistor**

2SB781

### **DESCRIPTION**

- Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= -50V(Min)
- · Good Linearity of hFE
- · Fast Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

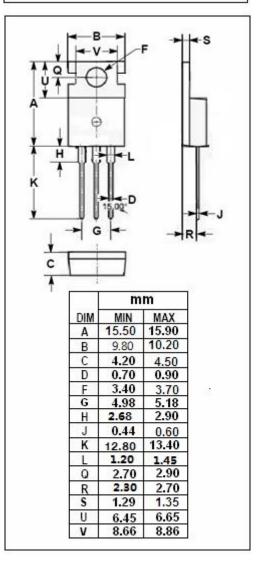
# PIN: 1 Base 2 Collector 3 Emitter TO-220C package

### **APPLICATIONS**

 Designed for use in general purpose power amplifier and switching applications

### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL           | PARAMETER  | VALUE   | UNIT          |
|------------------|--|---------|---------------|
| V <sub>CBO</sub> | Collector-Base Voltage                             | -50     | V             |
| V <sub>CEO</sub> | Collector-Emitter Voltage                          | -50     | V             |
| V <sub>EBO</sub> | Emitter-Base Voltage                               | -5      | V             |
| Ic               | Collector Current-Continuous                       | -4      | А             |
| I <sub>CM</sub>  | Collector Current-Peak                             | -6      | А             |
| Pc               | Collector Power Dissipation @ T <sub>C</sub> =25°C | 30      | W             |
| TJ               | Junction Temperature                               | 150     | $^{\circ}$    |
| T <sub>stg</sub> | Storage Temperature Range                          | -55~150 | ${\mathbb C}$ |



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### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

| SYMBOL               | PARAMETER                            | CONDITIONS                                     | MIN | TYP. | MAX  | UNIT |
|----------------------|--------------------------------------|--|-----|------|------|------|
| V <sub>(BR)CEO</sub> | Collector-Emitter Breakdown Voltage  | I <sub>C</sub> = -10mA ; I <sub>B</sub> = 0    | -50 |      |      | V    |
| V <sub>CE(sat)</sub> | Collector-Emitter Saturation Voltage | I <sub>C</sub> = -4A; I <sub>B</sub> = -0.4A   |     |      | -1.0 | V    |
| V <sub>BE(on)</sub>  | Base-Emitter On Voltage              | I <sub>C</sub> = -0.5A ; V <sub>CE</sub> = -5V |     |      | -1.0 | V    |
| I <sub>CBO</sub>     | Collector Cutoff Current             | V <sub>CB</sub> = -50V ; I <sub>E</sub> = 0    |     |      | -100 | μА   |
| I <sub>EBO</sub>     | Emitter Cutoff Current               | V <sub>EB</sub> = -5V; I <sub>C</sub> = 0      |     |      | -10  | μА   |
| h <sub>FE1</sub>     | DC Current Gain                      | Ic= -0.5A; Vc= -5V                             | 60  |      | 320  |      |
| h <sub>FE2</sub>     | DC Current Gain                      | I <sub>C</sub> = -4A ; V <sub>CE</sub> = -5V   | 10  |      |      |      |
| f⊤                   | Current-Gain—Bandwidth Product       | I <sub>C</sub> =-0.5A; V <sub>CE</sub> = -10V  | 5   |      |      | MHz  |

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